



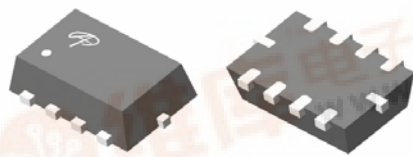
AON4602 Complementary Enhancement Mode Field Effect Transistor

General Description

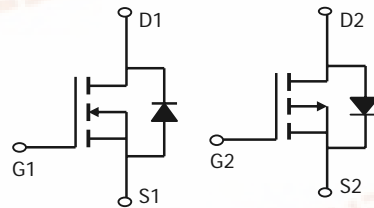
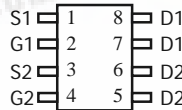
The AON4602 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications. Standard Product AON4602 is Pb-free (meets ROHS & Sony 259 specifications). AON4602L is a Green Product ordering option. AON4602 and AON4602L are electrically identical.

Features

	n-channel	p-channel	
V_{DS} (V)	20V	-20V	
I_D	4.2A	-3.4A	($V_{GS} = \pm 4.5V$)
$R_{DS(ON)} < 50m\Omega$		$< 90m\Omega$	($V_{GS} = \pm 4.5V$)
$R_{DS(ON)} < 63m\Omega$		$< 120m\Omega$	($V_{GS} = \pm 2.5V$)
$R_{DS(ON)} < 87m\Omega$		$< 160m\Omega$	($V_{GS} = \pm 1.8V$)



DFN3X2



n-channel

p-channel

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	20	-20	V
Gate-Source Voltage	V_{GS}	± 8	± 8	V
Continuous Drain Current ^A	I_D	4.2	-3.4	A
$T_A=25^\circ C$		3.2	-2.7	
Pulsed Drain Current ^B	I_{DM}	15	-15	
Power Dissipation	P_D	1.4	1.7	W
		$T_A=25^\circ C$	0.9	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Thermal Characteristics: n-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	70	90	$^\circ C/W$
$t \leq 10s$		100	125	
Maximum Junction-to-Ambient ^A	$R_{\theta JL}$	63	80	$^\circ C/W$
Steady-State				

Thermal Characteristics: p-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	49	75	$^\circ C/W$
$t \leq 10s$		81	100	
Maximum Junction-to-Ambient ^A	$R_{\theta JL}$	37	45	$^\circ C/W$
Steady-State				

AON4602

n-channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±8V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	0.4	0.7	1	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	15			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =4.2A T _J =125°C		41 58	50 70	mΩ
		V _{GS} =2.5V, I _D =3.7A		52	63	mΩ
		V _{GS} =1.8V, I _D =3.2A		67	87	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =4.2A		11		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.8	1	V
I _S	Maximum Body-Diode Continuous Current				2	A
DYNAMIC PARAMETERS						
C _{ISS}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz		436		pF
C _{OSS}	Output Capacitance			66		pF
C _{RSS}	Reverse Transfer Capacitance			44		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		3		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =4.2A		6.2		nC
Q _{gs}	Gate Source Charge			1.6		nC
Q _{gd}	Gate Drain Charge			0.5		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =5V, V _{DS} =10V, R _L =2.7Ω, R _{GEN} =6Ω		5.5		ns
t _r	Turn-On Rise Time			6.3		ns
t _{D(off)}	Turn-Off DelayTime			40		ns
t _f	Turn-Off Fall Time			12.7		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =4A, di/dt=100A/μs		12.3		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =4A, di/dt=100A/μs		3.5		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev0 : Jan. 2006

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

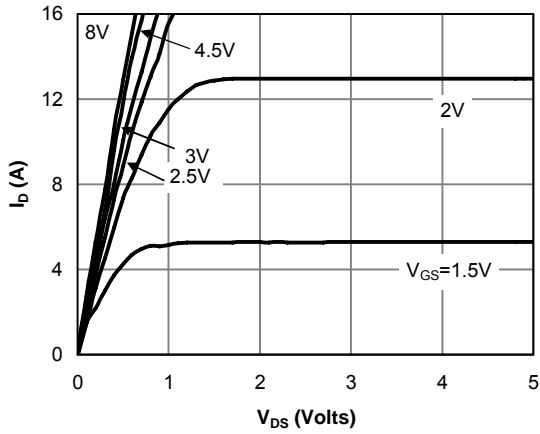


Fig 1: On-Region Characteristics

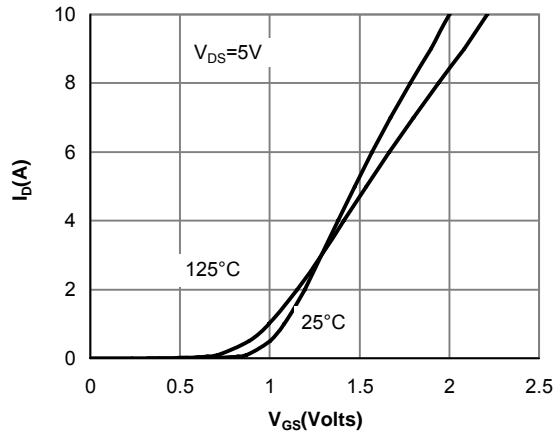


Figure 2: Transfer Characteristics

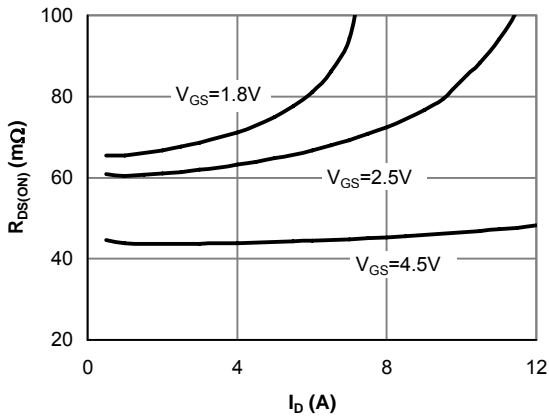


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

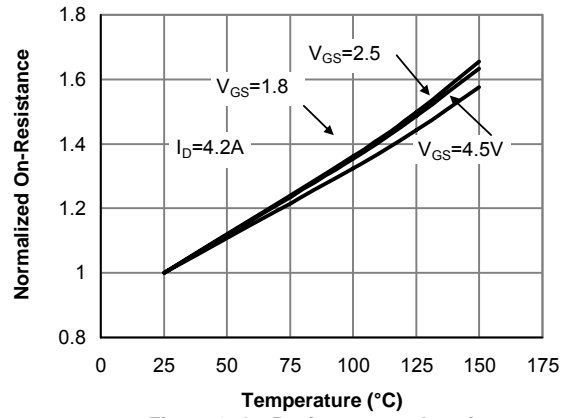


Figure 4: On-Resistance vs. Junction Temperature

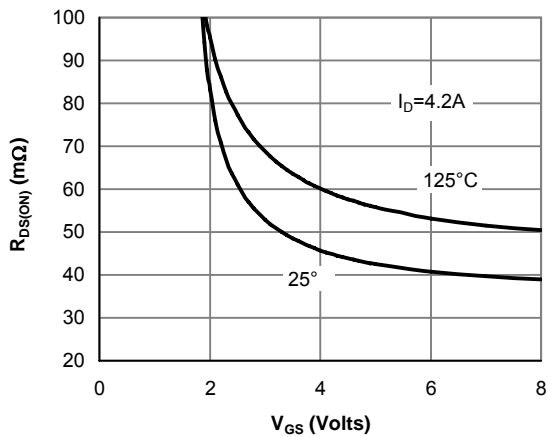


Figure 5: On-Resistance vs. Gate-Source Voltage

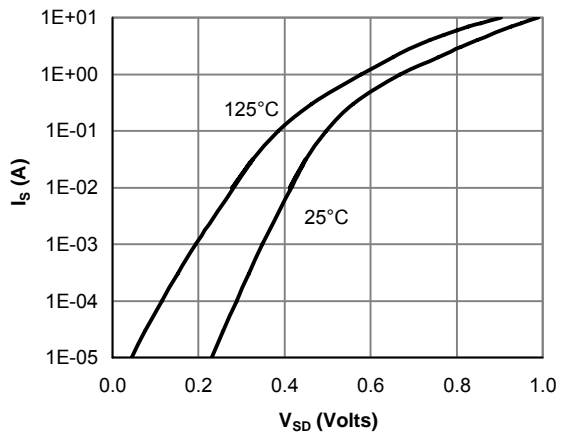


Figure 6: Body-Diode Characteristics

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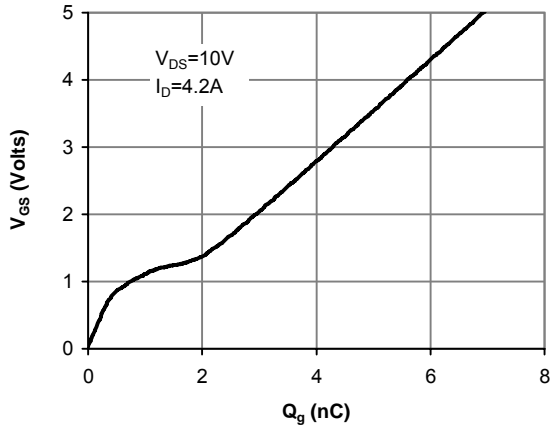


Figure 7: Gate-Charge Characteristics

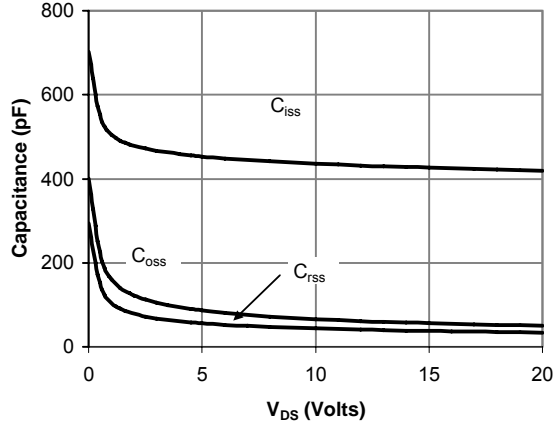


Figure 8: Capacitance Characteristics

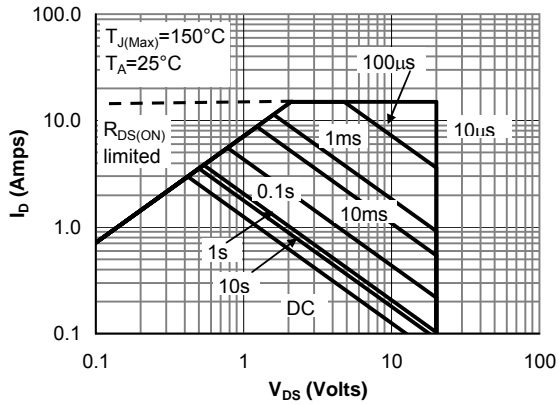


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

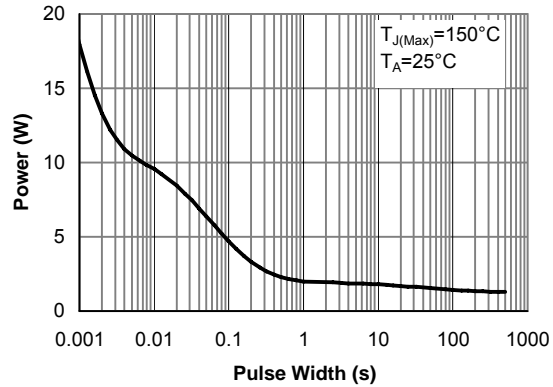


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

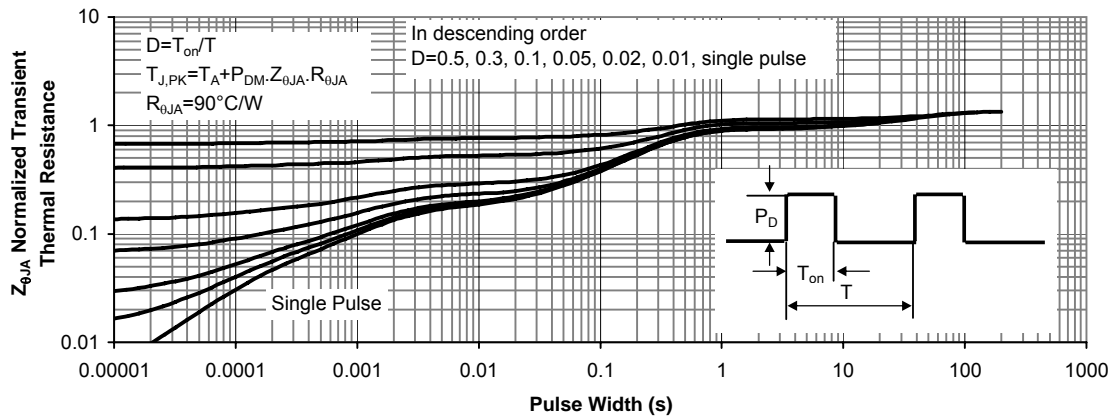


Figure 11: Normalized Maximum Transient Thermal Impedance

p-channel MOSFET Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-16V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±8V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-0.3	-0.63	-1	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-15			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-3.4A T _J =125°C		73 102	90 125	mΩ
		V _{GS} =-2.5V, I _D =-2.5A		95	120	mΩ
		V _{GS} =-1.8V, I _D =-1.5A		123	160	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-3.4A	4	7		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.83	-1	V
I _S	Maximum Body-Diode Continuous Current				-2	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance			540		pF
C _{oss}	Output Capacitance	V _{GS} =0V, V _{DS} =-10V, f=1MHz		72		pF
C _{rss}	Reverse Transfer Capacitance			49		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		12		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge			6.1		nC
Q _{gs}	Gate Source Charge	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-3.8A		0.6		nC
Q _{gd}	Gate Drain Charge			1.6		nC
t _{D(on)}	Turn-On DelayTime			10		ns
t _r	Turn-On Rise Time	V _{GS} =-4.5V, V _{DS} =-10V, R _L =2.6Ω, R _{GEN} =3Ω		12		ns
t _{D(off)}	Turn-Off DelayTime			44		ns
t _f	Turn-Off Fall Time			22		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-3.8A, dI/dt=100A/μs		21		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-3.8A, dI/dt=100A/μs		7.5		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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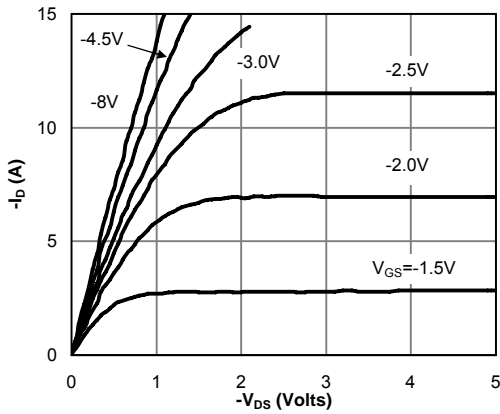


Fig 1: On-Region Characteristics

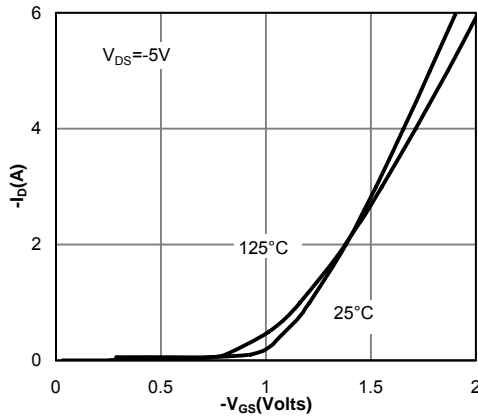


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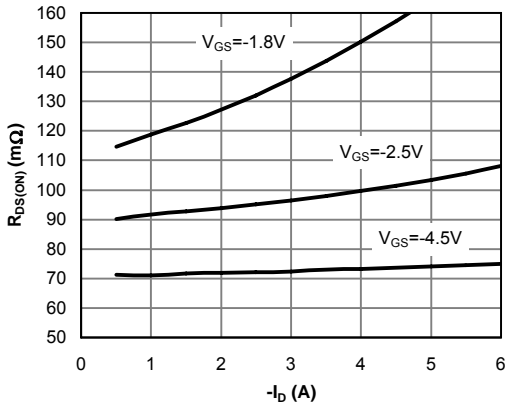


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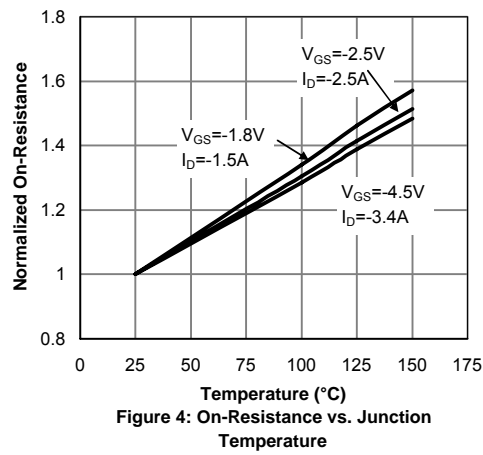


Figure 4: On-Resistance vs. Junction Temperature

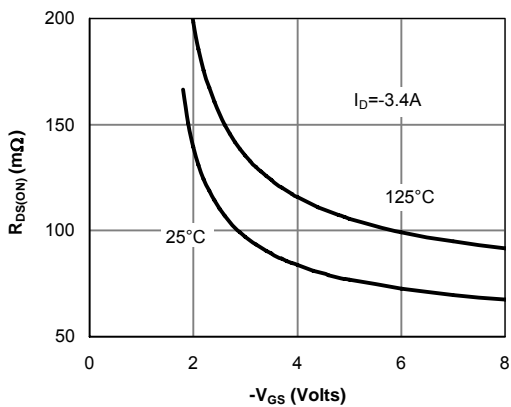


Figure 5: On-Resistance vs. Gate-Source Voltage

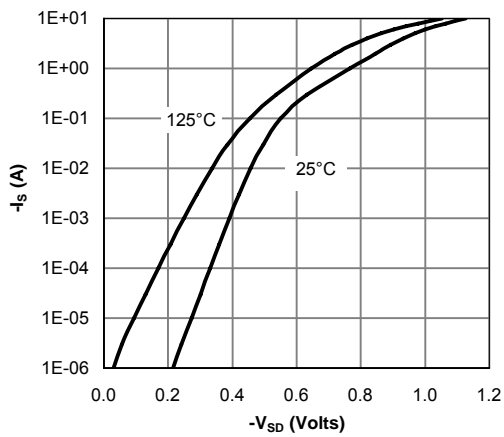


Figure 6: Body-Diode Characteristics

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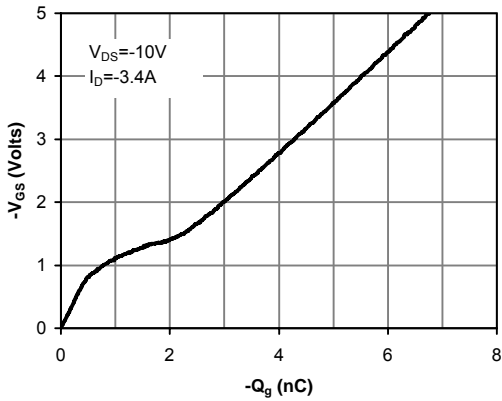


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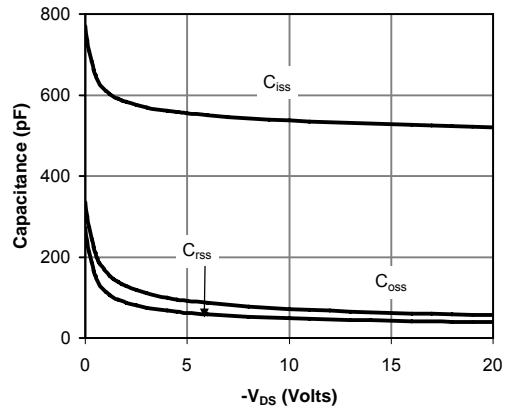


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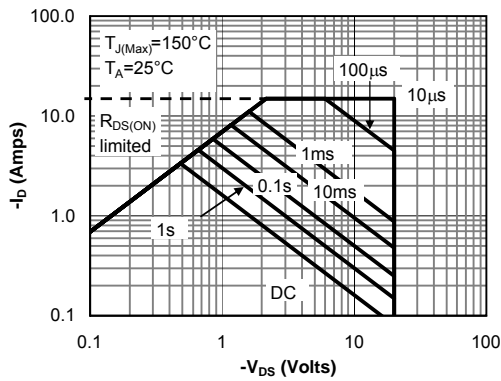


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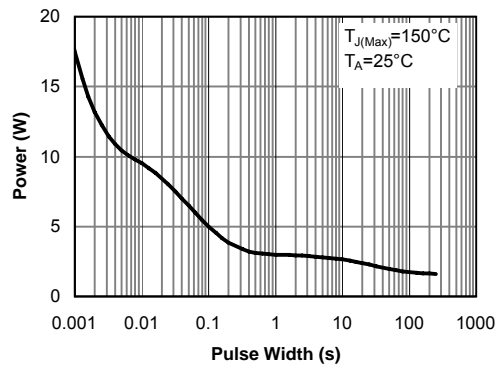


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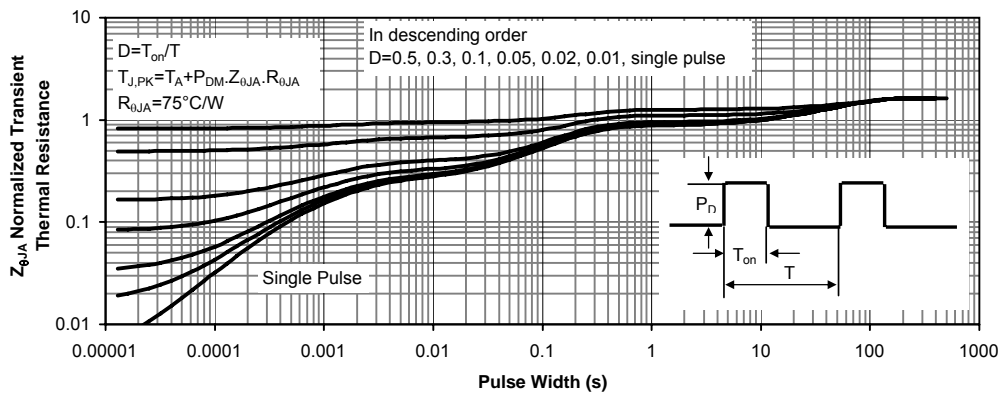


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